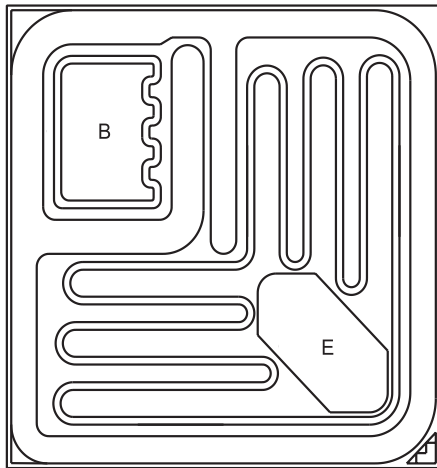


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	111 X 111 MILS
Die Thickness	10 MILS
Base Bonding Pad Area	20 X 30 MILS
Emitter Bonding Pad Area	20 X 26 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au/Cr/Ni/Au - 6,000Å

GEOMETRY



BACKSIDE COLLECTOR

R1

GROSS DIE PER 5 INCH WAFER

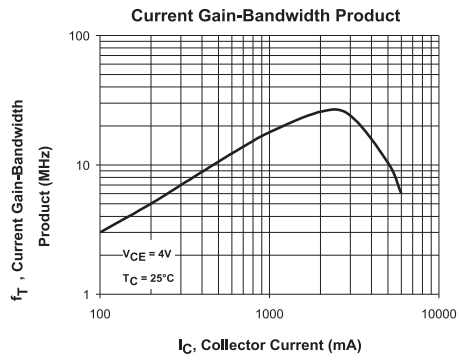
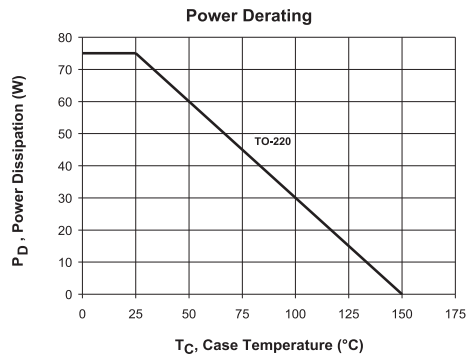
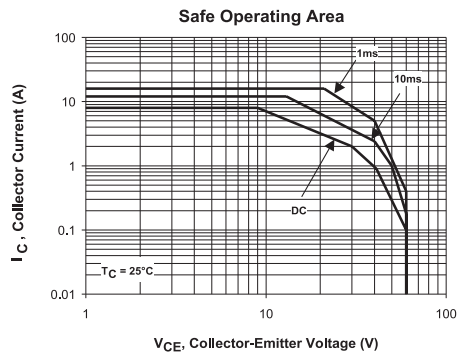
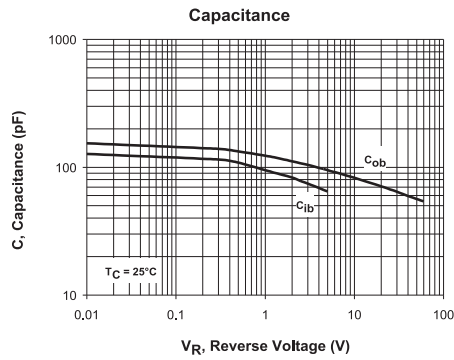
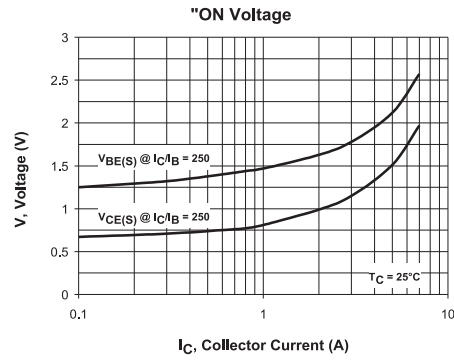
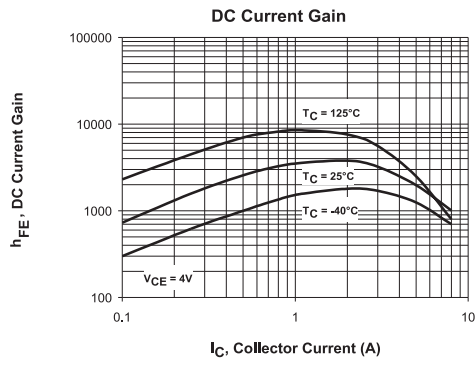
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PRINCIPAL DEVICE TYPES

2N6040
2N6041
2N6042
2N6299

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (1-August 2002)



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